

UTC UNISONIC TECHNOLOGIES CO., LTD

BCP68

NPN SILICON TRANSISTOR

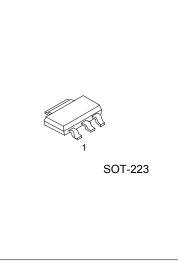
NPN MEDIUM POWER TRANSISTOR

FEATURES

- * High current (max. 1 A)
- * Low voltage (max. 20 V).
- * Complementary to UTC BCP69

APPLICATIONS

* General purpose switching and amplification under high current conditions.



Lead-free: BCP68L Halogen-free: BCP68G

ORDERING INFORMATION

Ordering Number			Pin Assignment			Dooking		
Normal	Lead Free Plating	Halogen Free	Package	1	2	3	Packing	
BCP68-xx-AA3-R	BCP68L-xx-AA3-R	BCP68G-xx-AA3-R	SOT-223	В	С	Е	Tape Reel	

BCP68L-xx-AA3-R		
	(1)Packing Type	(1) R: Tape Reel
	(2)Package Type	(2) AA3: SOT-223
	(3)Rank	(3) xx: refer to Classification of h⊧⊧
	(4)Lead Plating	(4) L: Lead Free Plating, Blank: Pb/Sn

ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage (Open Emitter)		V _{CBO}	32	V
Collector-Emitter Voltage (Open Base)		V _{CEO}	20	V
Emitter-Base Voltage (Open Collector)		V _{EBO}	5	V
Collector Current	DC	lc	1	А
Collector Current	Peak	Iсм	2	А
Peak Base Current		I _{BM}	200	mA
Total Power Dissipation (Ta ≤ 25°C)		PD	1.35	W
Junction Temperature		TJ	150	°C
Operating Temperature		T _{OPR}	-45 ~ +150	°C
Storage Temperature		T _{STG}	-65 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Thermal Resistance From Junction To Ambient	θ _{JA}	91	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C = 1A, I _B =100mA			500	mV
Ross Emitter Voltage		I _C = 5mA, V _{CE} = 10V		620		mV
Base-Emitter Voltage	V _{BE}	$I_C = 1A$, $V_{CE} = 1V$			1	V
Collector Cut-off Current		I _E = 0, V _{CB} = 25V			100	nA
Collector Cut-on Current	I _{CBO}	I _E = 0, V _{CB} = 25V, T _J = 150°C			10	μA
Emitter Cut-off Current	I _{EBO}	$I_{\rm C} = 0, V_{\rm EB} = 5V$			100	nA
		I _C = 5mA, V _{CE} = 10V	50			
DC Current Gain	. –	I _C = 500mA, V _{CE} = 1V	85		375	
		$I_{C} = 1A, V_{CE} = 1V$	60			
Collector Capacitance	Cc	I _E = i _e = 0, V _{CB} = 5V, f = 1MHz		48		рF
Transition Frequency	f _T	I _C = -10mA, V _{CE} = -5V, f = 100MHz	40			MHz
DC Current Gain Ratio of the	h _{FE1}				1.6	
Complementary Pairs	h _{FE2}	I _C = 0.5A, V _{CE} = 1V			1.6	

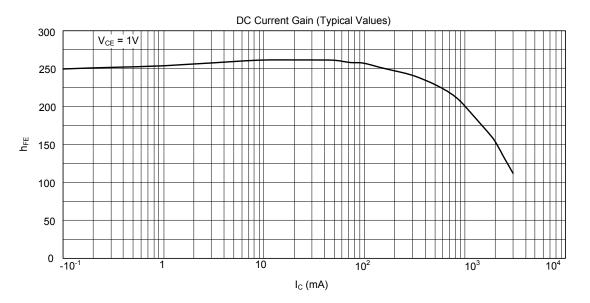
CLASSIFICATION OF h_{FE}

RANK	16	25
RANGE	100~250	160~375



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■ TYPICAL CHARACTERISTIC



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